

App. No. 10/604,065  
Response dated September 28, 2005  
Reply to Office Action of June 29, 2005

Please replace the pending abstract of the disclosure with the following amended abstract:

#### ABSTRACT

Wafer holder for semiconductor manufacturing and semiconductor manufacturing device in which the holder is installed, the wafer holder having a wafer-carrying surface, wherein the isothermal rating of its wafer-carrying surface is enhanced. In the wafer holder having a wafer-carrying surface, by making the spacing of electrodes for supplying power to electrical circuits formed either on a surface other than the wafer-carrying surface of the wafer holder, or else inside it, 10% or more of the wafer holder thickness, the temperature distribution in the wafer-carrying surface can be brought to within  $[\pm 1.0\%]$   $\pm 1.0\%$ . The electrical circuits can be heater circuits, electrostatic-chuck electrode circuits, RF electrode circuits, and high-voltage electrode circuits. One or more metals selected from the group being tungsten, molybdenum and tantalum preferably are incorporated into the portion of the power-supply electrodes that is directly connected to the circuits.